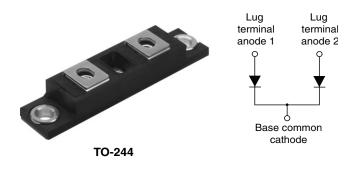
Vishay High Power Products

HEXFRED[®] Ultrafast Soft Recovery Diode, 210 A



SHA

PRODUCT SUMMARY				
I _{F(AV)}	210 A			
V _R	600 V			
$I_{F(DC)}$ at T_C	120 A at 100 °C			

FEATURES

- Very low Q_{rr} and t_{rr}
- Lead (Pb)-free
- Designed and qualified for industrial level

BENEFITS

- Reduced RFI and EMI
- Reduced snubbing

DESCRIPTION

HEXFRED[®] diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. An extensive characterization of the recovery behavior for different values of current, temperature and dl/dt simplifies the calculations of losses in the operating conditions. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for power converters, motors drives and other applications where switching losses are significant portion of the total losses.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Cathode to anode voltage	V _R		600	V	
		T _C = 25 °C	235		
Continuous forward current	I _F	T _C = 100 °C	120	A	
Single pulse forward current	I _{FSM}	Limited by junction temperature	600		
Non-repetitive avalanche energy	E _{AS}	L = 100 μ H, duty cycle limited by maximum T _J	2.2	mJ	
	Р	T _C = 25 °C	463	w	
Maximum power dissipation	PD	T _C = 100 °C	185	vv	
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	°C	

ELECTRICAL SPECIFICATIONS PER LEG ($T_J = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		600	-	-	
Maximum forward voltage	V _{FM}	I _F = 105 A		-	1.38	1.9	V
		I _F = 210 A	See fig. 1	-	1.6	2.25	
	I _F = 105 A, T _J = 125 °C			-	1.3	1.56	1
Maximum reverse leakage current	I _{RM}	$T_{\rm J} = 125 ^{\circ}\text{C}, V_{\rm R} = 480 \text{V}$ See fig. 2		-	1.8	6.0	mA
Junction capacitance	CT	V _R = 200 V See fig. 3		-	200	300	pF
Series inductance	L _S	From top of terminal hole to mounting plane		-	6.0	-	nH



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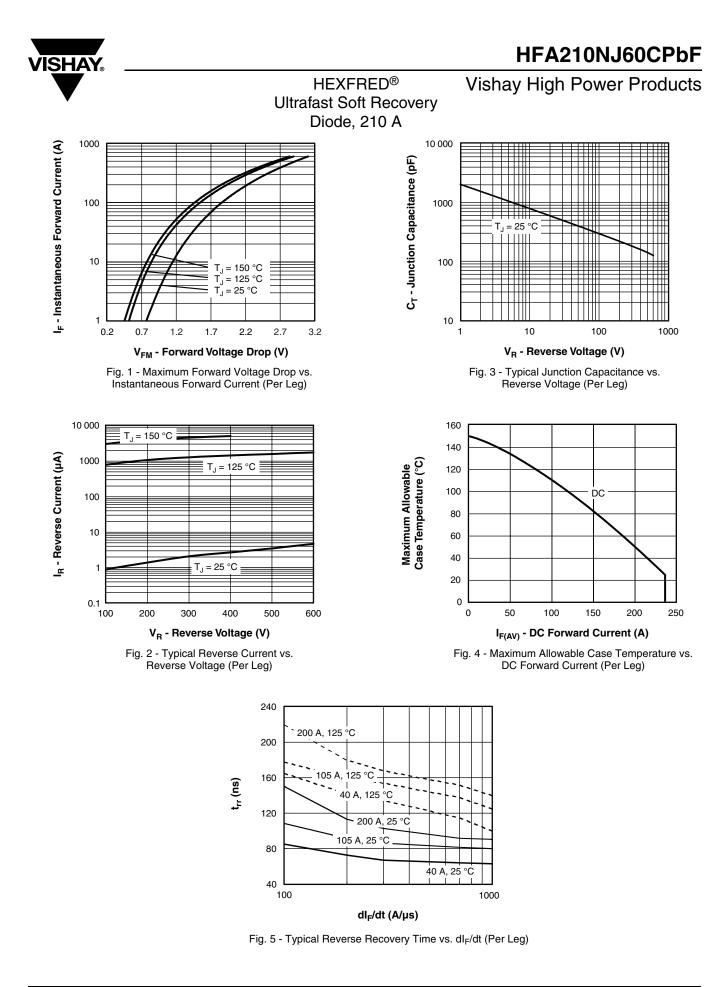
DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25 \text{ °C}$ unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS	
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		-	35	-		
Reverse recovery time See fig. 5	t _{rr}	T _J = 25 °C		-	90	140	ns	
		T _J = 125 °C		-	160	240		
Peak recovery current		T _J = 25 °C		-	10	18	•	
See fig. 6	I _{RRM}	IRRM	T _J = 125 °C	$I_{\rm F} = 105 {\rm A}$	-	15	30	A
Reverse recovery charge	Q _{rr}	T _J = 25 °C	dI _F /dt = 200 A/μs V _B = 200 V	-	450	1300		
See fig. 7		T _J = 125 °C		-	1200	3600	nC	
Peak rate of recovery current d	dl _{(rec)M} /dt	T _J = 25 °C		-	310	-	- A/μs	
		T _J = 125 °C		-	240	-		

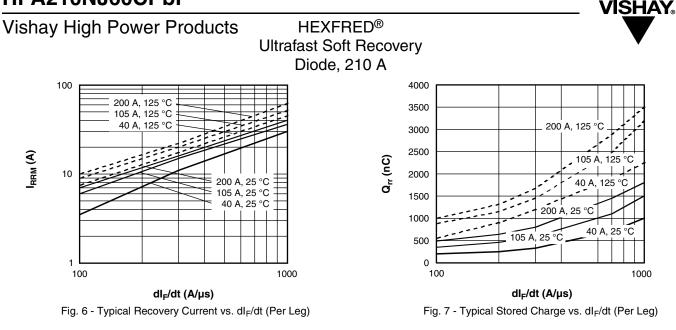
THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature	range	T _J , T _{Stg}	- 55	-	150	°C	
Thermal resistance, junction to case	per leg	R _{thJC} R _{thCS}	-	-	0.27	°C/W K/W	
	per module		-	-	0.135		
Typical thermal resistance, case to heatsink			-	0.10	-		
Weight			-	68	-	g	
Weight			-	2.4	-	oz.	
Mounting torque ⁽¹⁾			30 (3.4)	-	40 (4.6)		
Mounting torque center hole Terminal torque			12 (1.4)	-	18 (2.1)	N ⋅ m (lbf ⋅ in)	
			30 (3.4)	-	40 (4.6)	()	
Vertical pull			-	-	80	line in	
2" lever pull			-	-	35	lbf ⋅ in 35	

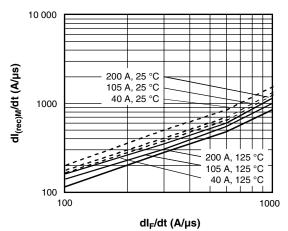
Note

(1) Mounting surface must be smooth, flat, free of burrs or other protrusions. Apply a thin even film or thermal grease to mounting surface. Gradually tighten each mounting bolt in 5 to 10 lbf · in steps until desired or maximum torque limits are reached











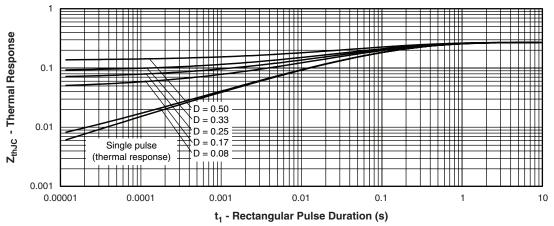


Fig. 9 - Maximum Thermal Impedance Z_{thJC} Characteristics (Per Leg)



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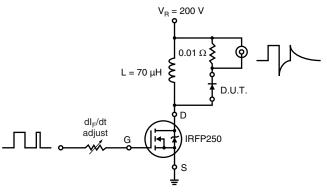
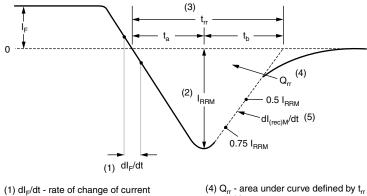


Fig. 10 - Reverse Recovery Parameter Test Circuit



through zero crossing

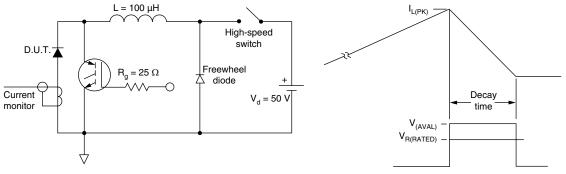
(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

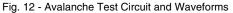
and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

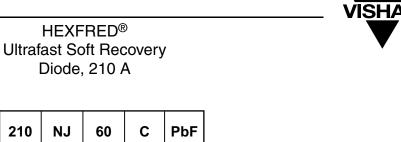
(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 11 - Reverse Recovery Waveform and Definitions



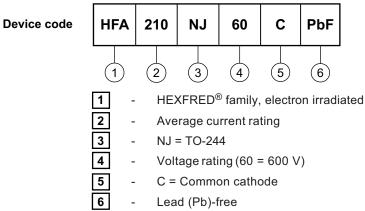


⁽²⁾ I_{BBM} - peak reverse recovery current



ORDERING INFORMATION TABLE

Vishay High Power Products



LINKS TO RELATED DOCUMENTS				
Dimensions	http://www.vishay.com/doc?95021			

HEXFRED[®]

Diode, 210 A



Vishay

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